

## Patent Abstracts of Japan

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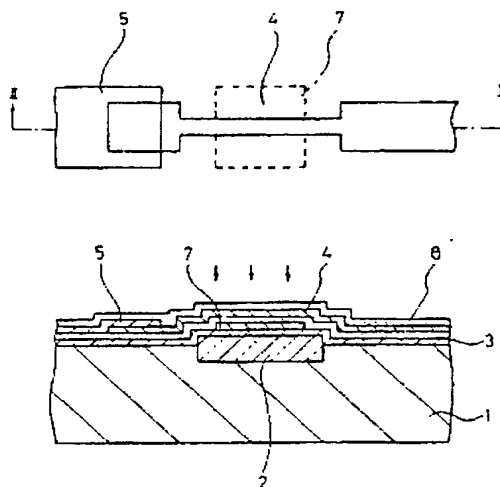
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TITLE : SEMICONDUCTOR DEVICE



**ABSTRACT :** PURPOSE: To enable a link to be melted down with laser beams having sufficient output by a method wherein an absorptive layer absorbing laser beams is provided immediately below a link to be melted down with laser beams.

CONSTITUTION: A link 4 is composed of a poly Si interconnection comprising a thin insulating film 3 formed on the surface of thick insulating film 2 formed on a semiconductor substrate 1 to be formed into an interconnection structure. An Al interconnection 5 is connected to the end of link 4 while a low temperature CVD protective film 6 is formed on the surface to protect the link 4 and the interconnection 5 against atmosphere. An absorptive layer 7 provided immediately below the link 4 is made of a material shielding the layer 7 from laser beams. In such a constitution, even if any laser output and pulse width are specified sufficiently to melt down the link 4, all the laser beams after melting down the link 4 can be absorbed into the layer 7 doing no damage to the surface of substrate 1 at all.

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